

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. (currently amended): A compound semiconductor light-emitting device comprising: a substrate having majoran upper surface; and a device side surface; and havinga light-emitting layer provided on the majorupper surface of said substrate, wherein at least a part of a substrate portion of the device side surface has longitudinalrecessed portions inwardly extended in a side direction of the device perpendicularto the upper surface of the substrate, and the recessed portions have a semi-circular shape in cross section parallelto the upper surface of the substrate, and

wherein the depth of the recessed portion is a radius of the semi-circular shape in a direction parallel to the upper surface of the substrate, and the height of the recessed portion is at least 20  $\mu\text{m}$  in the side direction of the device perpendicular to the upper surface of the surface of the substrate, and

wherein a distance of 4 to 40  $\mu\text{m}$  is maintained between the adjacent recessed portions.

2. (original): A light-emitting device according to claim 1, wherein at least a part of a compound semiconductor portion of the device side surface has recessed portions in a side direction of the device.

3. (original): A light-emitting device according to claim 1, wherein the light-emitting layer comprises an n-type or p-type compound semiconductor and is of the pn junction type.

4. (original): A light-emitting device according to claim 1, wherein the substrate is selected from the group consisting of a sapphire, a SiC and a III-V Group compound semiconductor single crystal.

5. (canceled).

6. (original): A light-emitting device according to claim 1, wherein individual ones of the recessed portions have a depth of 0.5 to 10  $\mu\text{m}$  and a width of 1 to 20  $\mu\text{m}$ .

7. (original): A light-emitting device according to claim 1, wherein the compound semiconductor light-emitting device is of the flip-chip type.

8-17. (canceled).

18. (original): A lamp comprising a compound semiconductor light-emitting device of claim 1.

19. (original): A source of light comprising a lamp of claim 18.